

SUBSTRATE PROPERTY	MGSi4NTDNAs	MGSi4NTDNSb	MGSi4NTDNP	MGSi4NTDPB
Diameter	100 mm			
Growth Method	NTD			
Orientation	<100>, <110>, <111>			
Carrier Type	N-type			P-type
Dopant	As	Sb	P	B
Resistivity	30-600 $\Omega\cdot\text{cm}$			
Thickness	525 $\mu\text{m} \pm 25 \mu\text{m}$			
TTV	$\leq 10 \mu\text{m}$			
Bow	$\leq 40 \mu\text{m}$			

*The other specifications can be customized according to customer's requirements